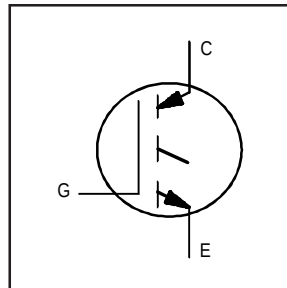


IRG4CC81UB



600 V
Size 8.1
Ultra-Fast Speed
6" Wafer

Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	4.5V Max.	$I_C = 10A$, $T_J = 25^\circ C$, $V_{GE} = 15V$
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600V Min.	$T_J = 25^\circ C$, $I_{CES} = 250\mu A$, $V_{GE} = 0V$
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 6.0V Max.	$V_{GE} = V_{CE}$, $T_J = 25^\circ C$, $I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	300 μA Max.	$T_J = 25^\circ C$, $V_{CE} = 600V$
I_{GES}	Gate-to-Emitter Leakage Current	$\pm 11 \mu A$ Max.	$T_J = 25^\circ C$, $V_{GE} = \pm 20V$

Mechanical Data

Norminal Backmetal Composition, Thickness:	Cr-Ni / V-Ag (1kA-2kA-.2.5kA)
Norminal Front Metal Composition, Thickness:	99% Al, 1% Si (4 microns)
Dimensions:	0.523" x 0.523"
Wafer Diameter:	150mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5249
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	Consistent throughout same wafer lot
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions	For optimum electrical results, die attach temperature should not exceed 300C

Reference Standard IR packaged part (for design) : GA200TS60U

Die Outline

	NOTES: - ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES) - CONTROLLING DIMENSION: (INCH). - LETTER DESIGNATION: S = SOURCE SK = SOURCE KELVIN G = GATE IS = CURRENT SENSE - DIMENSIONAL TOLERANCES: BONDING PADS: < 0.635 TOLERANCE = +/- 0.013 WIDTH < (.0250) TOLERANCE = +/- (.0005) & < 0.635 TOLERANCE = +/- 0.025 LENGTH < (.0250) TOLERANCE = +/- (.0010) OVERALL DIE: < 1.270 TOLERANCE = +/- 0.102 WIDTH < (.050) TOLERANCE = +/- (.004) & < 0.635 TOLERANCE = +/- 0.203 LENGTH < (.050) TOLERANCE = +/- (.008) - UNLESS OTHERWISE NOTED ALL DIE ARE GEN III
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